

TO-92 Plastic-Encapsulate Transistors

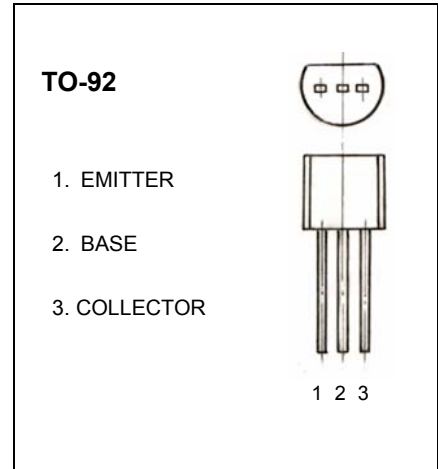
A42 TRANSISTOR (NPN)

FEATURES

High voltage

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	500	mA
P_C	Collector Power Dissipation	625	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, junction to Ambient	200	$^\circ\text{C}/\text{mW}$
$R_{\theta JC}$	Thermal Resistance, unction to Case	83.3	$^\circ\text{C}/\text{mW}$



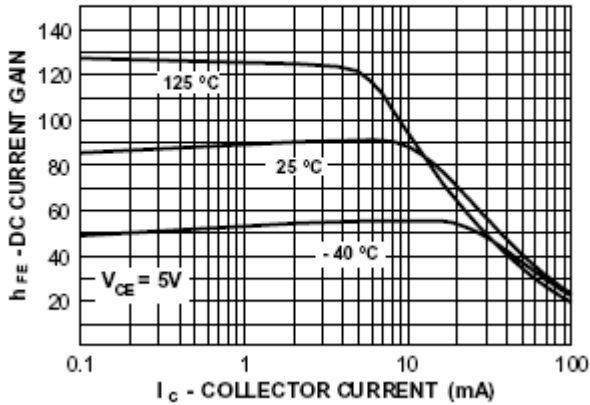
ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=200\text{V}, I_E=0$			0.25	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10\text{V}, I_C=1\text{mA}$	60			
	$h_{FE(2)}$	$V_{CE}=10\text{V}, I_C=10\text{mA}$	80		250	
	$h_{FE(3)}$	$V_{CE}=10\text{V}, I_C=30\text{mA}$	75			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=20\text{mA}, I_B=2\text{mA}$			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=20\text{mA}, I_B=2\text{mA}$			0.9	V
Transition frequency	f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=30\text{MHz}$	50			MHz

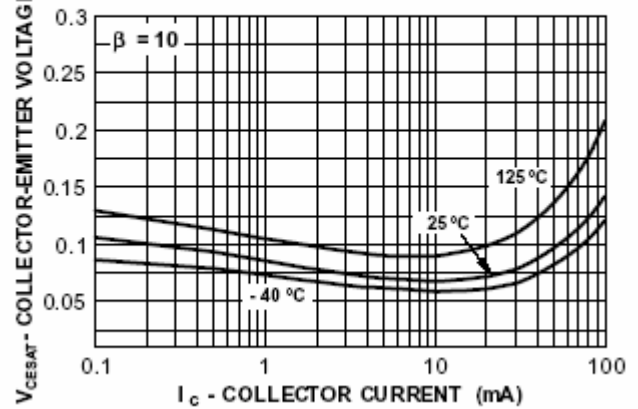
CLASSIFICATION OF $h_{FE(2)}$

Rank	A	B ₁	B ₂	C
Range	80-100	100-150	150-200	200-250

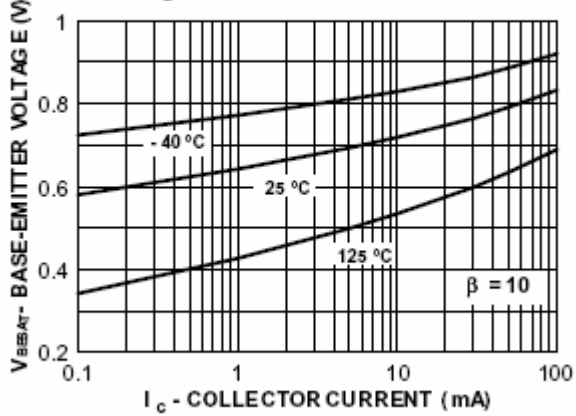
DC Current Gain vs Collector Current



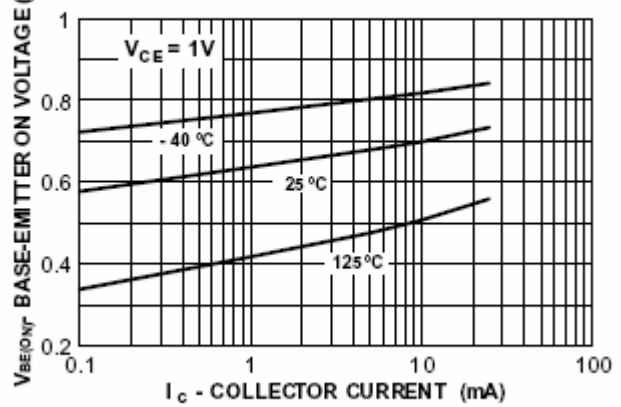
Collector-Emitter Saturation Voltage vs Collector Current



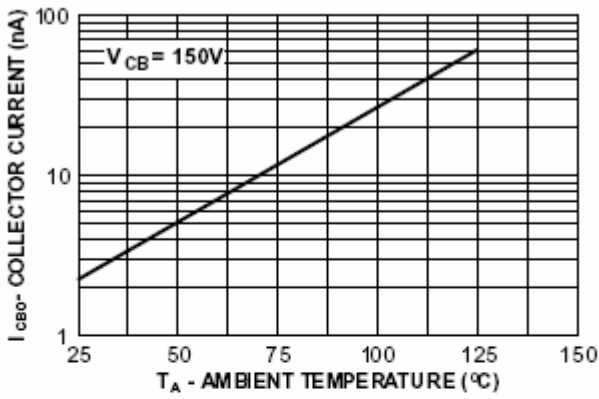
Base-Emitter Saturation Voltage vs Collector Current



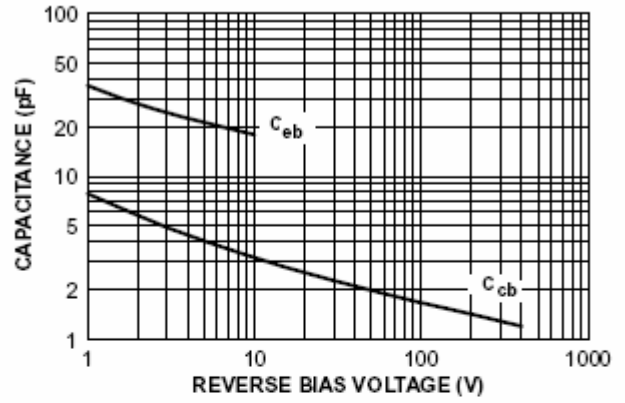
Base-Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature



Collector-Base and Emitter-Base Capacitance vs Reverse Bias Voltage



Power Dissipation vs Ambient Temperature

